Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1-6 (Canceled)

Claim 7 (Currently Amended): A semiconductor device comprising:

[[(a)]] a cross substrate comprising at least one resin sealed layer of a cross member, said at least one resin sealed layer of a cross member having warp threads and weft threads, wherein a portion of at least one of the warp threads and weft threads include a plurality of conductive thread-like wire members disposed substantially parallel to one another, with the wire members electrically insulated from one another, and [[an]] a bump electrode ~~portion~~ formed at one region of the thread-like wire members;

[[(b)]] a heat-dissipating plate having a high heat transfer coefficient; and

[[(c)]] a semiconductor element having a reverse surface side and a circuit forming surface side, the circuit forming surface side being mounted to the cross substrate, and the heat-dissipating plate being sealed at the reverse surface side ~~surface~~.

Claim 8 (Currently Amended): A semiconductor device comprising:

[[(a)]] a cross substrate comprising at least one resin sealed layer of a cross member, said at least one resin sealed layer of a cross member having warp threads and weft threads, wherein a portion of at least one of the warp threads and weft threads include a plurality of conductive thread-like wire members disposed substantially parallel to one another, with the wire members electrically insulated from one another, and [[an]] a bump electrode ~~portion~~ formed at one region of the thread-like wire members; and

[[(b)]] a semiconductor element having a reverse surface side and a circuit forming surface side, the circuit forming surface side being fixed to the cross substrate, and a conductive layer being disposed in a layer covering the reverse surface side.

Claim 9 (Currently Amended): A semiconductor substrate comprising:

a semiconductor element having a surface with a plurality of electrodes thereat;

a plurality of conductive members which extend in a predetermined first direction, [[with]] each conductive member electrically connected to a corresponding electrode of the semiconductor element by respective bump electrodes;

a plurality of insulative members which extend in a second direction ~~transverse~~ perpendicular to the first direction, and which are disposed so as to traverse regions between adjacent conductive members; and

a sealing resin, the conductive members having surfaces and ~~the conductive~~

~~members and the electrodes having connected portions~~[,]] the sealing resin sealing at least the [[said]] surfaces and ~~connected portions, and leaving~~ the bump electrodes so that at least one portion of the plurality of conductive members is exposed.

Claim 10 (Currently Amended): A method of mounting a semiconductor element comprising ~~the steps of~~:

[[(a)]] providing a cross member having at least one layer of warp threads and weft threads, wherein a portion of at least one of the warp threads and weft threads include a plurality of conductive thread-like wire members disposed substantially parallel to one another, with the wire members electrically insulated from one another, and an electrode portion formed at one region of the thread-like wire members;

[[(b)]] mounting a semiconductor element having an electrode forming surface with a plurality of electrodes thereat, onto said at least one layer of the cross member such that at least one of the plurality of electrodes of the semiconductor element is electrically connected to at least one of the thread-like wires; and

[[(c)]] sealing the cross member and the electrode forming surface of the semiconductor element with an insulating resin.

Claim 11 (Original): A method of mounting a semiconductor element according to claim 10, wherein the wire members have surfaces covered with an insulating material, except for a position of each wire member at which electrodes of the semiconductor

element are disposed.

Claim 12 (Currently Amended): A method of mounting a semiconductor element according to claim 10, wherein the cross member has at least two layers, such that orientations of wire members are different in each layer.

Claim 13 (Original): A method of mounting a semiconductor element according to claim 11, wherein at least one of the warp threads and one of the weft threads cross one another at a location, and are electrically connected to one another thereat.

Claim 14 (Original): A method of mounting a semiconductor element according to claim 11, wherein said cross substrate forms a casing having an interior with a surface, and the semiconductor element is provided at the surface of the interior of the casing.

Claim 15 (New): The semiconductor device according to claim 7, wherein the bump electrode is a solder bump.

Claim 16 (New): The semiconductor device according to claim 8, wherein the bump electrode is a solder bump.

Claim 17 (New): The semiconductor substrate according to claim 9, wherein the bump

electrodes are solder bumps.

Claim 18 (New): The semiconductor device according to claim 7, wherein the bump electrode electrically contacts one of the plurality of conductive thread-like members.

Claim 19 (New): The semiconductor device according to claim 8, wherein the bump electrode electrically contacts one of the plurality of conductive thread-like members.